

1. General description

Silicon Carbide MOSFET in a TO263-7L plastic package, designed for high frequency, high efficiency systems.



2. Features and benefits

- Low on-resistance
- Fast switching speed
- 0V turn-off gate voltage for simple gate drive
- Easy to parallel
- 100% UIS Tested
- Controllable dV/dt for optimized EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Switch Mode Power Supplies
- UPS
- Solar string inverter and solar optimizer
- EV Charger
- Motor Drives

4. Quick reference data

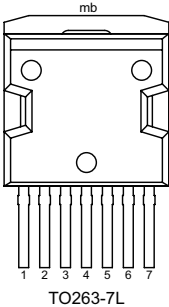
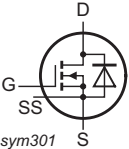
Table 1. Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		1700			V
I _D	drain current	V _{GS} = 18 V; T _{mb} = 25 °C		7.5			A
P _{tot}	total power dissipation	T _{mb} = 25 °C		91			W
T _j	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 15 V; I _D = 1 A; T _j = 25 °C		-	1000	-	mΩ
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 2 A; V _{DS} = 1200 V; V _{GS} = 0 V/18 V; T _j = 25 °C		-	12	-	nC
Q _{GD}	gate-drain charge			-	5	-	nC
Source-drain diode							
Q _r	recovered charge	I _{SD} = 1 A; di/dt = 500 A/μs; V _{DS} = 400 V; T _i = 25 °C		-	38	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	SS	source sense		
3-7	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2M1K0170B7	TO263-7L	WNSC2M1K0170B7J	Reel	800	TO263P-7L	12-Jun-2023

7. Marking

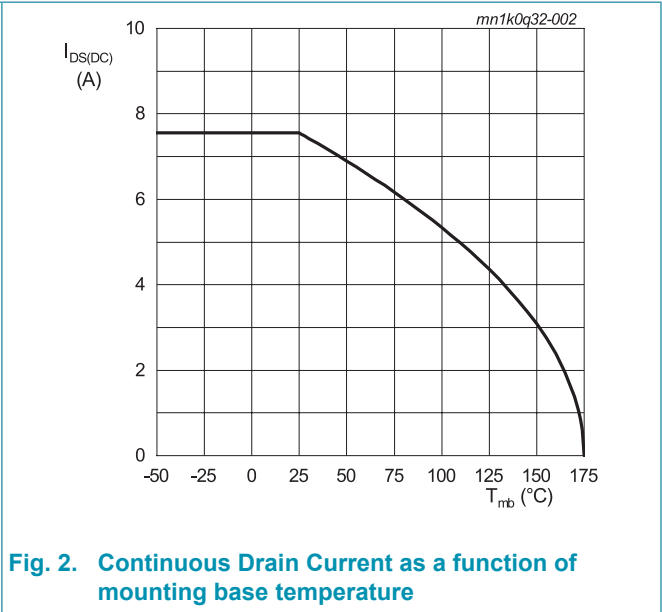
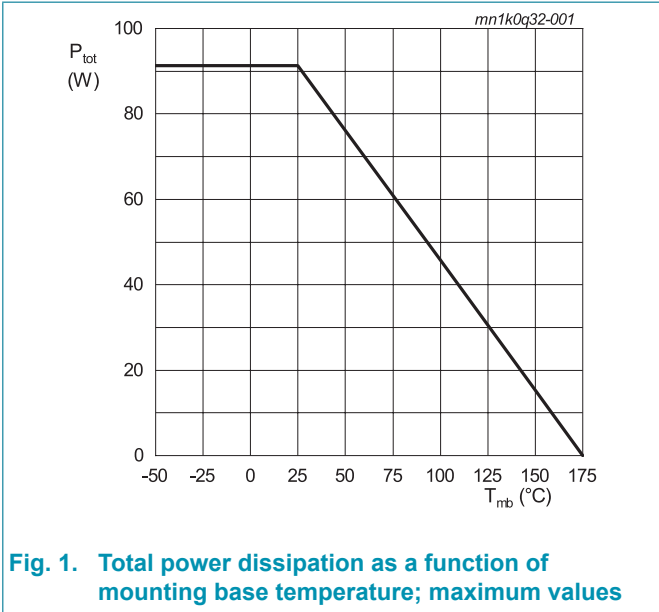
Table 4. Marking codes

Type number	Marking codes
WNSC2M1K0170B7	WNSC2M 1K0170B7

8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Vaules	Unit
V_{DS}	drain-source voltage	$25\text{ }^{\circ}\text{C} \leq T_J \leq 175\text{ }^{\circ}\text{C}$		1700	V
$V_{GS,max}$	gate-source voltage	Absolute maximum values		-10 to 22	V
$V_{GS,op}$	gate-source voltage	Recommended operational values		-5 to 18	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$		91	W
I_D	drain current	$V_{GS} = 18\text{ V}; T_{mb} = 25\text{ }^{\circ}\text{C}$		7.5	A
		$V_{GS} = 18\text{ V}; T_{mb} = 100\text{ }^{\circ}\text{C}$		5.3	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ }^{\circ}\text{C}$		20	A
E_{as}	single pulse drain-to-source avalanche	$I_{AS} = 7\text{ A}; L = 1\text{ mH}; V_{DD} = 100\text{ V}; T_{J(init)} = 25\text{ }^{\circ}\text{C}$		24.5	mJ
T_{stg}	storage temperature			-55 to 175	$^{\circ}\text{C}$
T_J	junction temperature			-55 to 175	$^{\circ}\text{C}$
$T_{sld(M)}$	peak soldering temperature			260	$^{\circ}\text{C}$



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	-	1.64	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	40	-	K/W

Note: Device is ESD sensitive. Handling precautions are recommended.

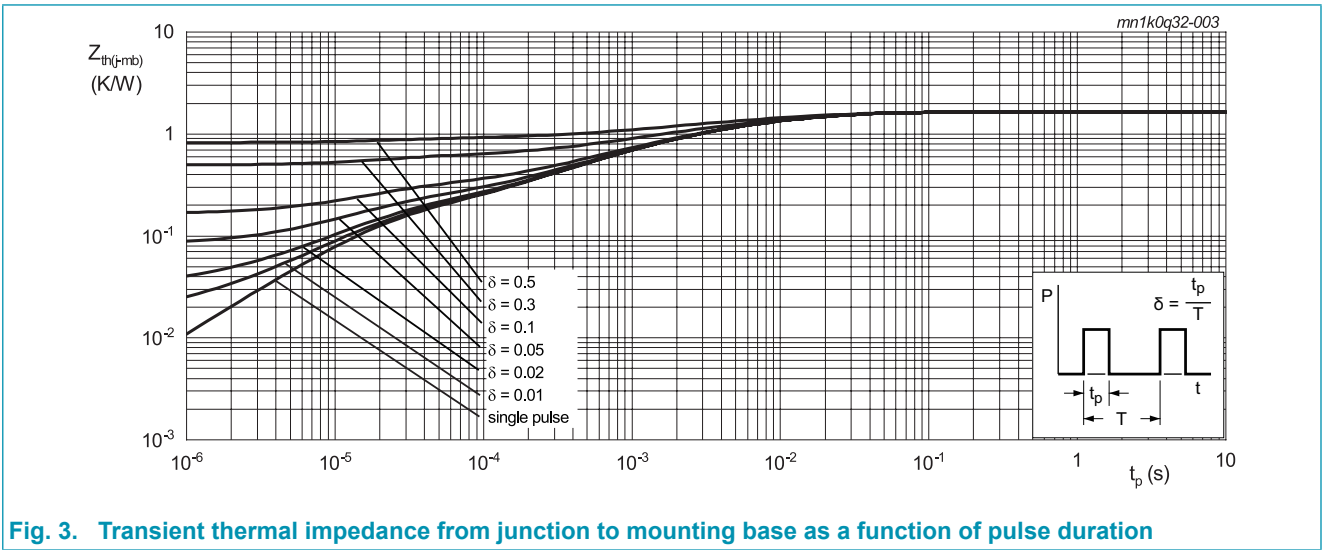
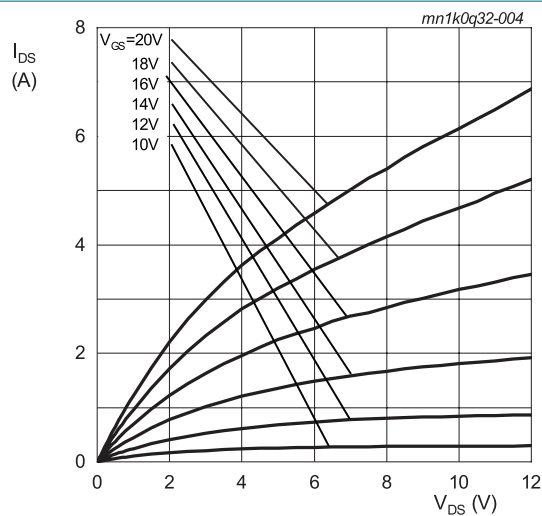


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

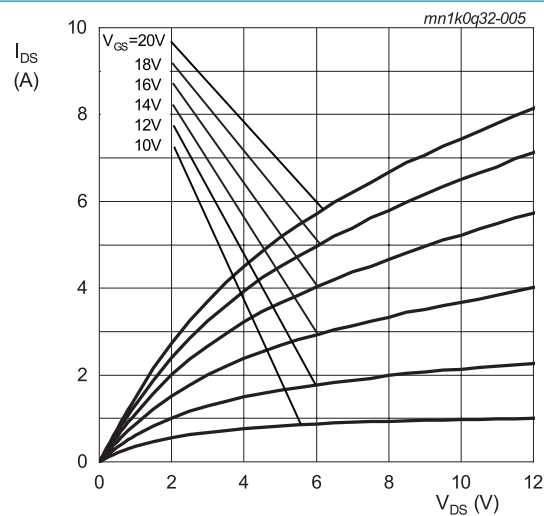
10. Characteristics

Table 7. Characteristics

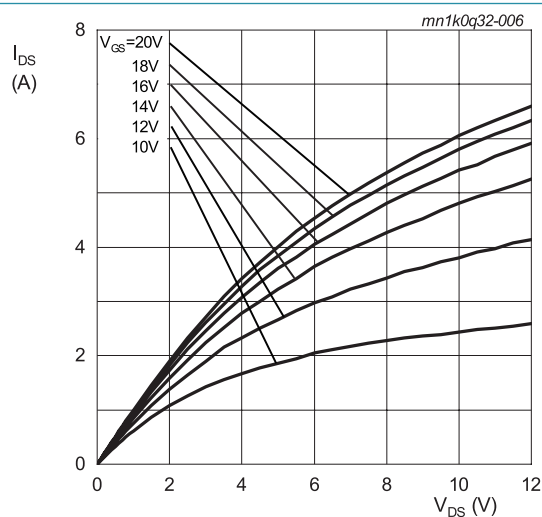
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 100 μA; V _{GS} = 0 V; T _J = 25 °C		1700	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 0.8 mA; V _{DS} = 10 V; T _J = 25 °C		2.3	3.2	4.2	V
		I _D = 0.8 mA; V _{DS} = 10 V; T _J = 150 °C		-	2.4	-	V
I _{DSS}	drain leakage current	V _{DS} = 1700 V; V _{GS} = 0 V; T _J = 25 °C		-	0.1	10	μA
		V _{DS} = 1700 V; V _{GS} = 0 V; T _J = 150 °C		-	1	-	μA
I _{GSS}	gate leakage current	V _{GS} = 18 V; V _{DS} = 0 V; T _J = 25 °C		-	10	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _J = 25 °C		-	10	100	nA
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 15 V; I _D = 1 A; T _J = 25 °C		-	1000	-	mΩ
		V _{GS} = 18 V; I _D = 1 A; T _J = 25 °C		-	750	1200	mΩ
		V _{GS} = 18 V; I _D = 1 A; T _J = 150 °C		-	1050	-	mΩ
R _G	gate resistance	f = 1 MHz; T _J = 25 °C		-	16	-	Ω
g _{fs}	transconductance	V _{DS} = 10 V; I _D = 1 A; T _J = 25 °C		-	0.5	-	S
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 2 A; V _{DS} = 1200 V; V _{GS} = 0 V/18 V; T _J = 25 °C		-	12	-	nC
Q _{GS}	gate-source charge			-	3.8	-	nC
Q _{GD}	gate-drain charge			-	5	-	nC
C _{iss}	input capacitance	V _{DS} = 1000 V; V _{GS} = 0 V; f = 1 MHz; T _J = 25 °C		-	225	-	pF
C _{oss}	output capacitance			-	15	-	pF
C _{rss}	reverse transfer capacitance			-	2.8	-	pF
E _{oss}	Coss stored energy			-	7.5	-	μJ
t _{d(on)}	turn-on delay time	V _{DS} = 1000 V; V _{GS} = -3 V/18 V; R _{G(ext)} = 5.1 Ω; I _D = 2 A; L = 1.4 mH; T _J = 25 °C		-	15	-	ns
t _r	rise time			-	21	-	ns
t _{d(off)}	turn-off delay time			-	19	-	ns
t _f	fall time			-	10	-	ns
E _{on}	turn-on energy (Body Diode FWD)			-	23	-	μJ
E _{off}	turn-off energy (Body Diode FWD)			-	3	-	μJ
Source-drain diode							
V _{SD}	source-drain voltage	V _{GS} = 0 V; I _F = 1 A; T _J = 25 °C		-	3.9	-	V
		V _{GS} = 0 V; I _F = 1 A; T _J = 150 °C		-	3.4	-	V
t _{rr}	reverse recovery time	I _{SD} = 1 A; di/dt = 500 A/μs; V _{DS} = 400 V; T _J = 25 °C		-	36	-	ns
Q _r	recovered charge			-	38	-	nC
I _{rrm}	reverse recovery current			-	1.8	-	A



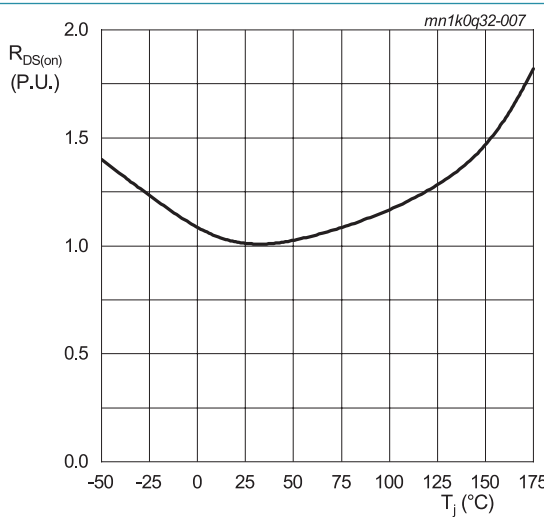
$T_j = -55\text{ }^{\circ}\text{C}; t_p < 200\text{ }\mu\text{s}$
Fig. 4. Output characteristics; drain current as a function of drain-source voltage; typical values



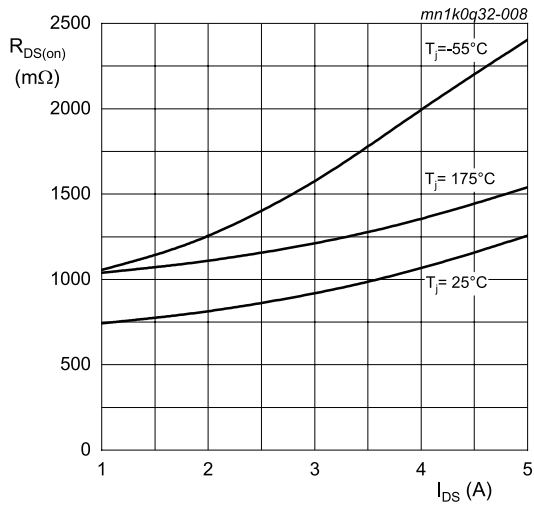
$T_j = 25\text{ }^{\circ}\text{C}; t_p < 200\text{ }\mu\text{s}$
Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values



$T_j = 150\text{ }^{\circ}\text{C}; t_p < 200\text{ }\mu\text{s}$
Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

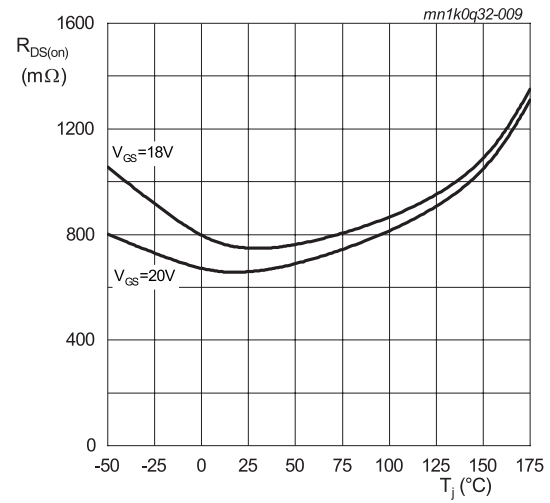


$I_{DS} = 1\text{ A}; V_{GS} = 18\text{ V}; t_p < 200\text{ }\mu\text{s}$
Fig. 7. Normalized drain-source on-state resistance as a function of junction temperature



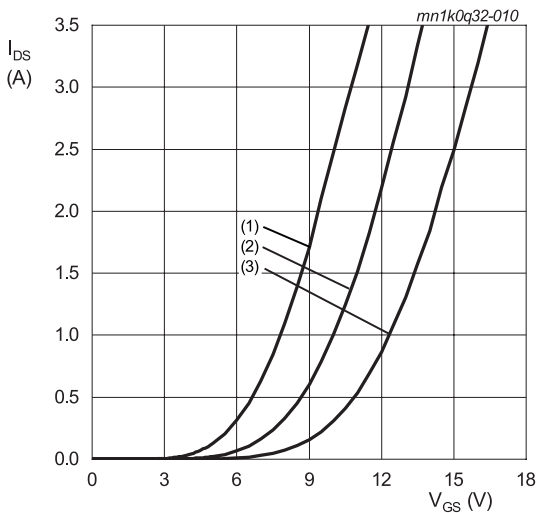
$V_{GS} = 18 \text{ V}$; $t_p < 200 \text{ } \mu\text{s}$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



$I_{DS} = 1 \text{ A}$; $t_p < 200 \text{ } \mu\text{s}$

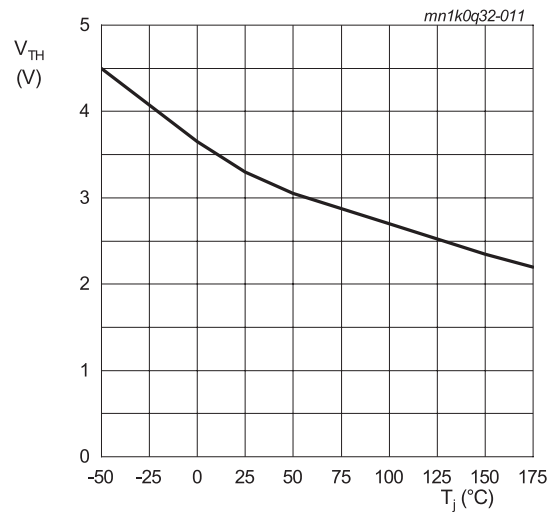
Fig. 9. Drain-source on-state resistance as a function of junction temperature



$V_{DS} = 10 \text{ V}$; $t_p < 200 \text{ } \mu\text{s}$

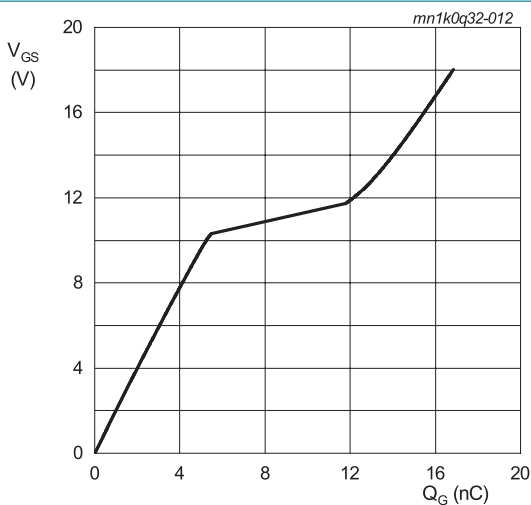
- (1) $T_J = 150 \text{ } ^\circ\text{C}$
- (2) $T_J = 25 \text{ } ^\circ\text{C}$
- (3) $T_J = -55 \text{ } ^\circ\text{C}$

Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values



$V_{DS} = 10 \text{ V}$; $I_{DS} = 0.8 \text{ mA}$

Fig. 11. Threshold voltage as a function of junction temperature



$I_{DS} = 2\text{ A}$; $I_{GS} = 0.1\text{ mA}$; $V_{DS} = 1200\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$
Fig. 12. Gate-source voltage as a function of gate charge; typical values

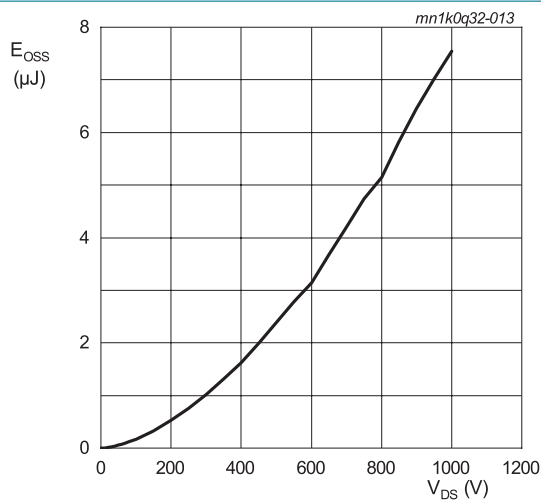
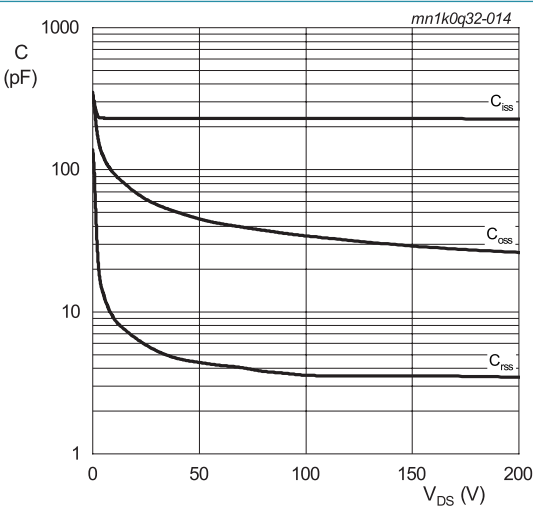
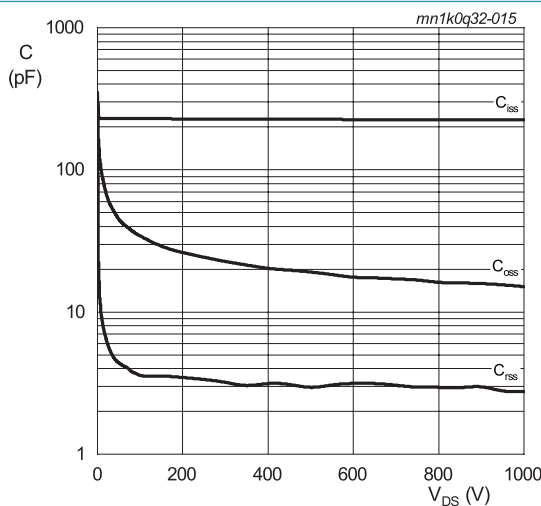


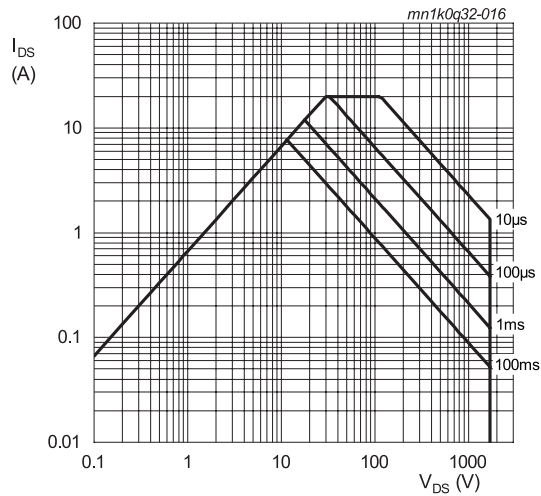
Fig. 13. Output capacitor stored energy as a function of drain-source voltage



$V_{DS} = 0 - 200\text{ V}$
 $T_j = 25\text{ }^{\circ}\text{C}$; $V_{AC} = 25\text{ mV}$; $f = 1\text{ MHz}$
Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

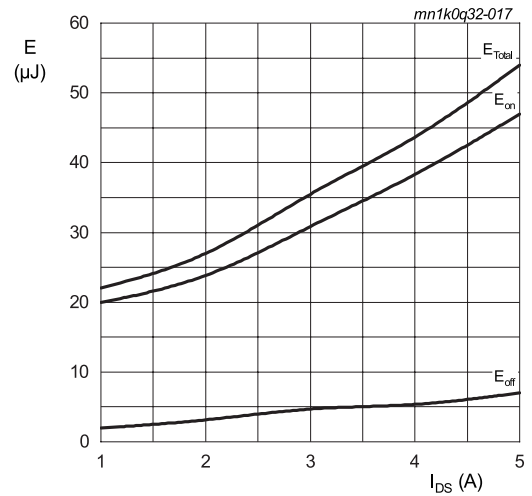


$V_{DS} = 0 - 1000\text{ V}$
 $T_j = 25\text{ }^{\circ}\text{C}$; $V_{AC} = 25\text{ mV}$; $f = 1\text{ MHz}$
Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



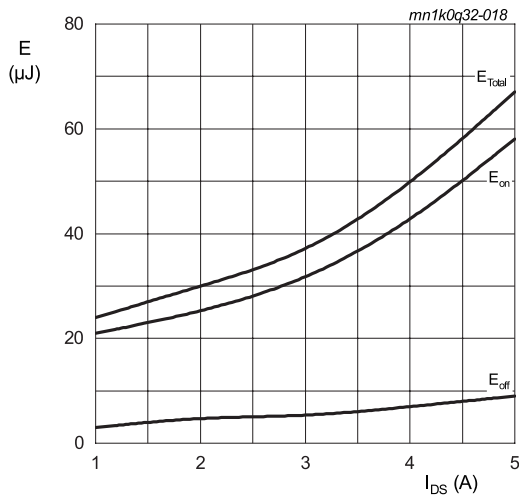
$T_j = 25\text{ }^{\circ}\text{C}$; $D = 0$
Parameter: t_p

Fig. 16. Forward bias safe operating area



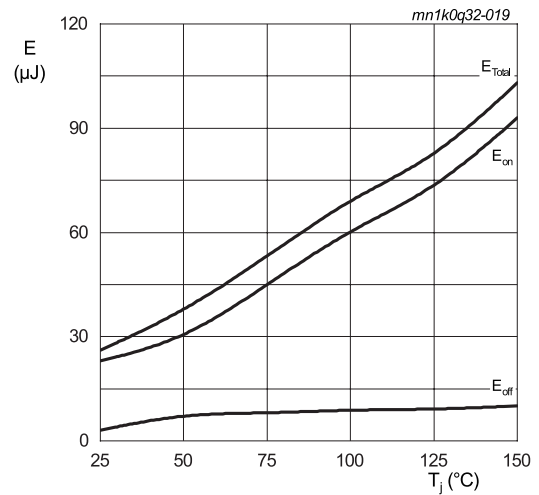
$T_j = 25\text{ }^{\circ}\text{C}$; $V_{DD} = 1000\text{ V}$; $R_{G(\text{ext})} = 5.1\text{ }\Omega$;
 $V_{GS} = -3\text{ V}/18\text{ V}$; FWD = WNSC2M1K0170B7
 $L = 1.4\text{ mH}$

Fig. 17. Clamped Inductive Switching Energy as a function of drain current



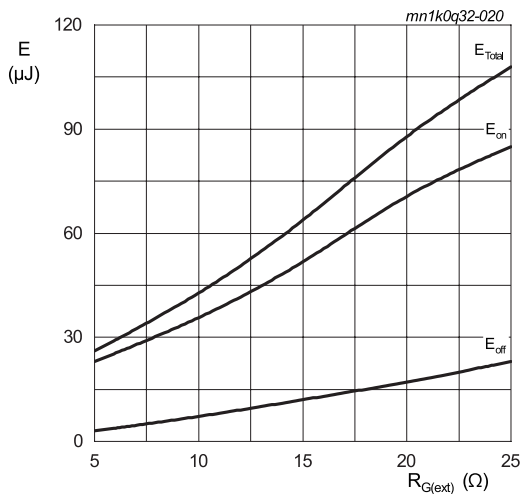
$T_j = 25\text{ }^{\circ}\text{C}$; $V_{DD} = 1200\text{ V}$; $R_{G(\text{ext})} = 5.1\text{ }\Omega$;
 $V_{GS} = -3\text{ V}/18\text{ V}$; FWD = WNSC2M1K0170B7
 $L = 1.4\text{ mH}$

Fig. 18. Clamped Inductive Switching Energy as a function of drain current



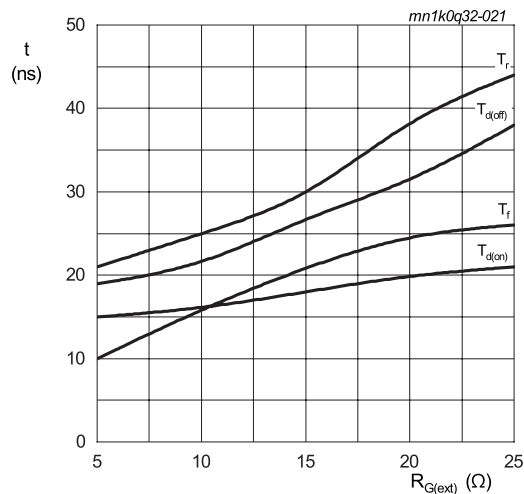
$I_{DS} = 2\text{ A}$; $V_{DD} = 1000\text{ V}$; $R_{G(\text{ext})} = 5.1\text{ }\Omega$;
 $V_{GS} = -3\text{ V}/18\text{ V}$; FWD = WNSC2M1K0170B7
 $L = 1.4\text{ mH}$

Fig. 19. Clamped Inductive Switching Energy as a function of junction temperature



$T_j = 25\text{ }^{\circ}\text{C}$; $V_{DD} = 1000\text{ V}$; $I_{DS} = 2\text{ A}$; $V_{GS} = -3\text{ V}/18\text{ V}$
FWD = WNSC2M1K0170B7; $L = 1.4\text{ mH}$

Fig. 20. Clamped Inductive Switching Energy as a function of external gate resistance



$T_j = 25\text{ }^{\circ}\text{C}$; $V_{DD} = 1000\text{ V}$; $I_{DS} = 2\text{ A}$; $V_{GS} = -3\text{ V}/18\text{ V}$
FWD = WNSC2M1K0170B7; $L = 1.4\text{ mH}$

Fig. 21. Switching time as a function of external gate resistance

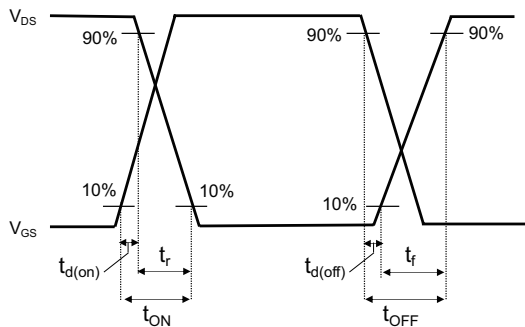
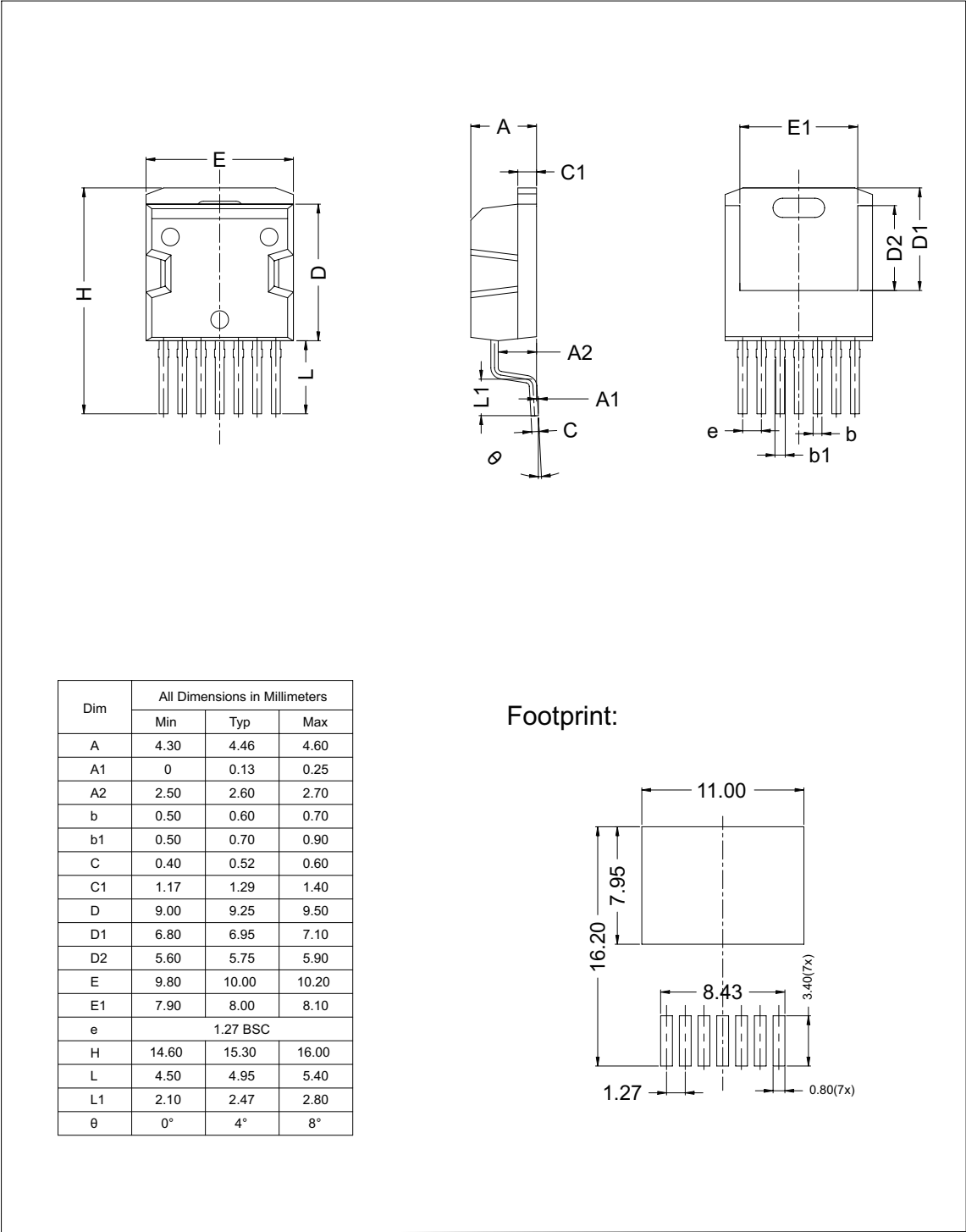


Fig. 22. Switching time definition

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

1. General description..... 1

2. Features and benefits 1

3. Applications 1

4. Quick reference data..... 1

5. Pinning information..... 2

6. Ordering information..... 2

7. Marking..... 2

8. Limiting values 3

9. Thermal characteristics 4

10. Characteristics..... 5

11. Package outline 11

12. Legal information 12

13. Contents 14

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